

SANYO

NPN Triple Diffused Planar Silicon Transistor

Ultrahigh-Definition CRT Display Horizontal Deflection Output Applications

Features

- High Speed : $t_r = 100\text{ns typ.}$
- High breakdown voltage : $V_{\text{CBO}} = 1500\text{V.}$
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.

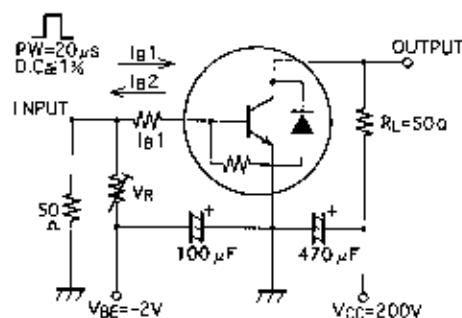
Absolute Maximum Ratings at Ta = 25°C

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$			unit
Collector-to-Base Voltage	V_{CBO}	1500	V
Collector-to-Emitter Voltage	V_{CEO}	800	V
Emitter-to-Base Voltage	V_{EB0}	6	V
Collector Current	I_C	8	A
Collector Current (Pulse)	I_{CP}	16	A
Collector Dissipation	P_C	3.0	W
	$T_c = 25^\circ\text{C}$	60	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

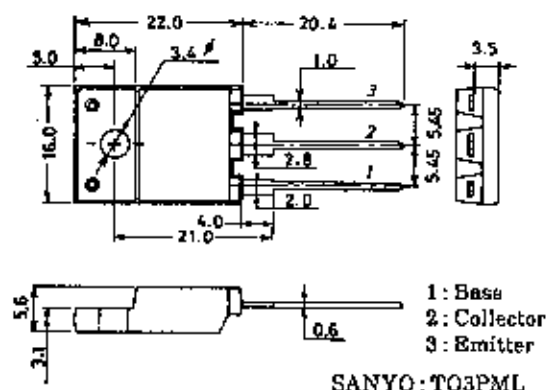
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800\text{V}, I_E = 0$			10	μA
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500\text{V}, R_{BE} = 0$			1.0	mA
Collector Sustaining Voltage	$V_{CEO(\text{SUS})}$	$I_C = 100\text{mA}, I_B = 0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			1.0	mA
C-E Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 5\text{A}, I_B = 1.25\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(\text{sat})}$	$I_C = 5\text{A}, I_B = 1.25\text{A}$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	20		30	
	$h_{FE(2)}$	$V_{CE} = 5\text{V}, I_C = 5\text{A}$	4		7	
Storage Time	t_{stg}	$I_C = 4\text{A}, I_{B1} = 0.8\text{A}, I_{B2} = -1.6\text{A}$			3.0	μs
Fall Time	t_f	$I_C = 4\text{A}, I_{B1} = 0.8\text{A}, I_{B2} = -1.6\text{A}$	0.1		0.2	μs

Switching Time Test Circuit



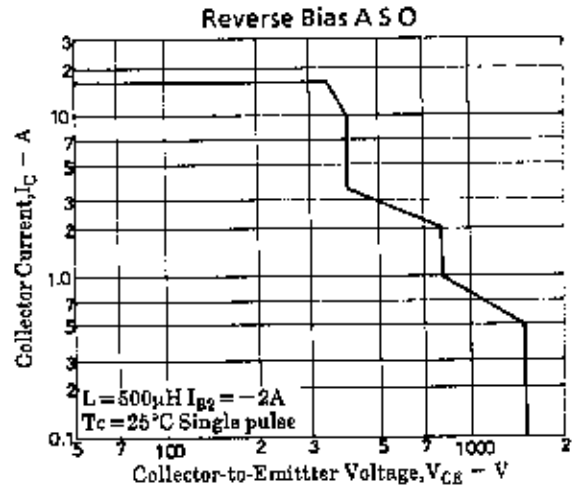
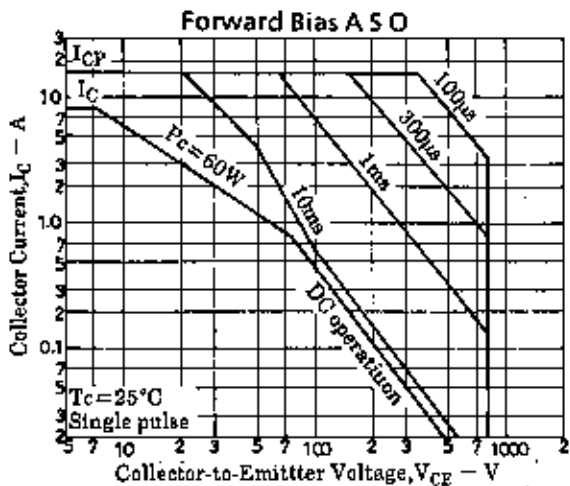
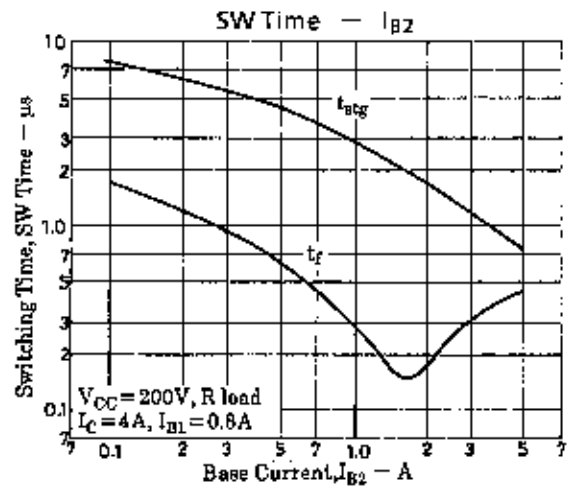
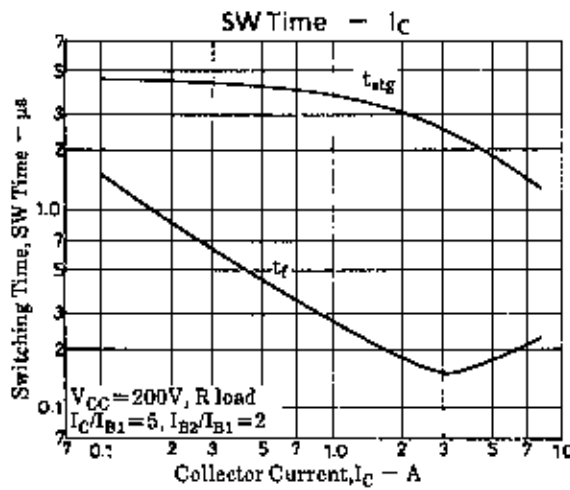
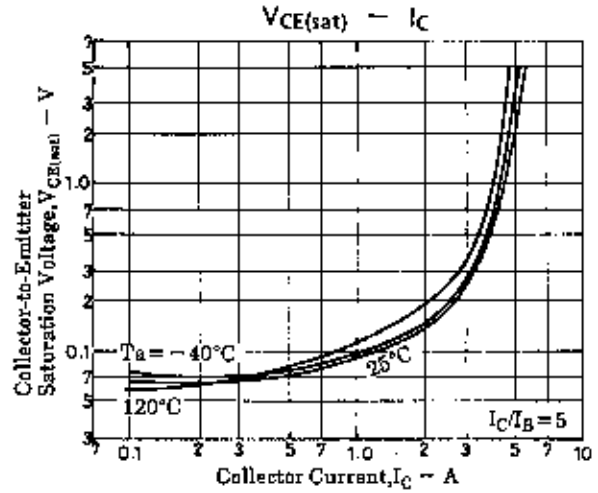
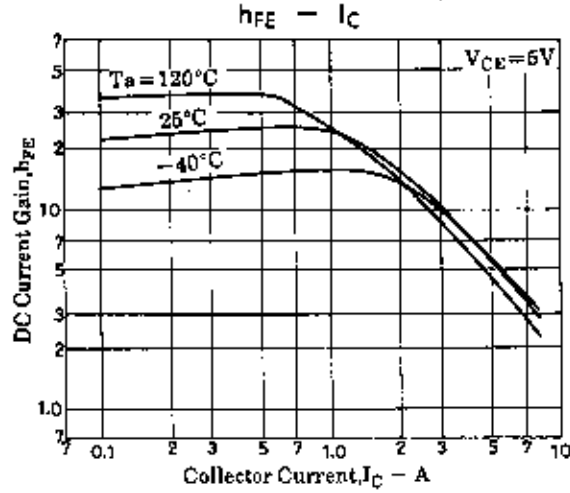
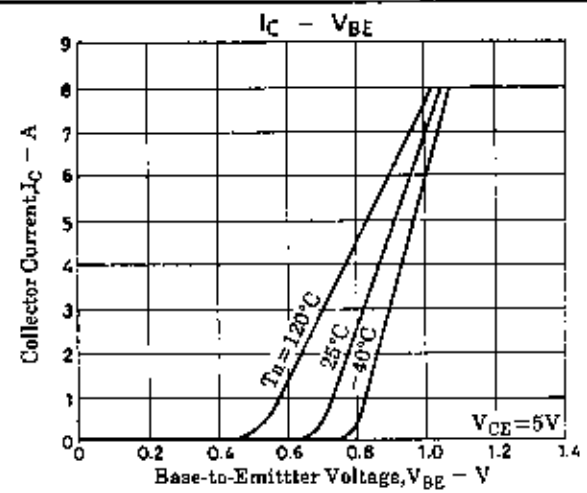
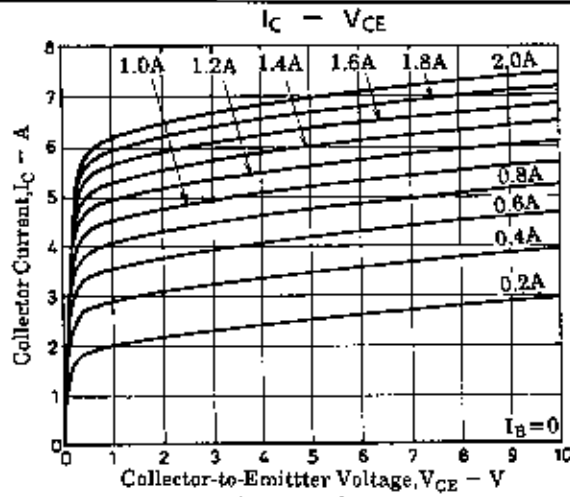
Package Dimensions 2039C
(unit : mm)

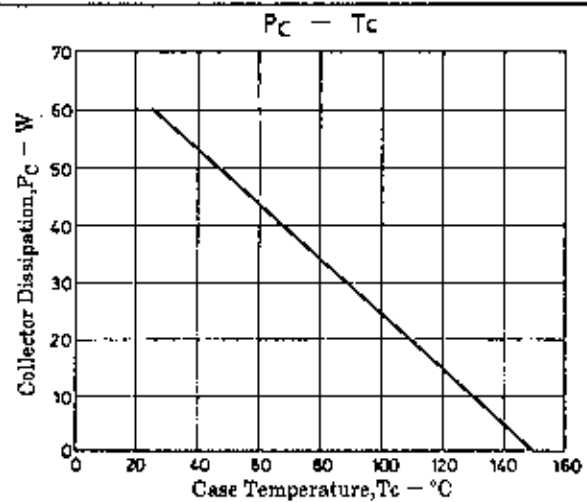
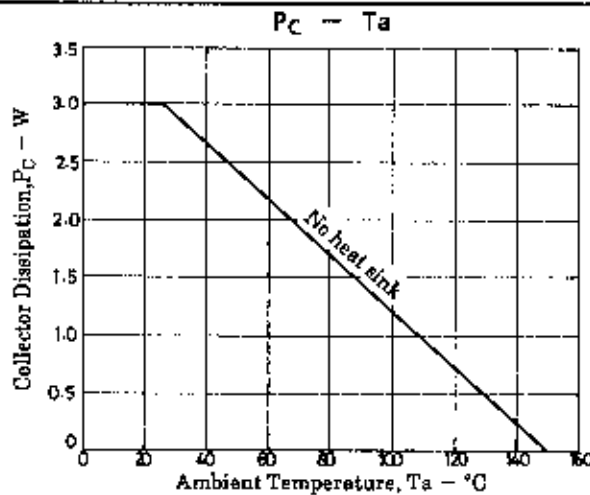


SANYO:TO3PML

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

11696YK (KOTO) TA-0585 No.5291-1/3





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